



N-Channel Enhancement-Mode MOS FETs

N 沟道增强型 MOS 场效应管

■ MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Rat 額定值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	BV_{DSS}	20	V
Gate- Source Voltage 柵極-源極電壓	V_{GS}	± 8	V
Drain Current (continuous) 漏極電流-連續	I_D	3.3	A
Drain Current (pulsed) 漏極電流-脉冲	I_{DM}	10	A
Total Device Dissipation 總耗散功率 $T_A=25^{\circ}\text{C}$ 環境溫度為 25°C	P_D	1000	mW
Junction 結溫	T_J	150	$^{\circ}\text{C}$
Storage Temperature 儲存溫度	T_{stg}	-55to+150	$^{\circ}\text{C}$

■ELECTRICAL CHARACTERISTICS 電特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如無特殊說明，溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓($I_D = 250\mu\text{A}, V_{GS}=0\text{V}$)	BV_{DSS}	20	—	—	V
Gate Threshold Voltage 柵極開啓電壓($I_D = 250\mu\text{A}, V_{GS} = V_{DS}$)	$V_{GS(th)}$	0.4	—	1.5	V
Diode Forward Voltage Drop 內附二極管正向壓降($I_S = 0.75\text{A}, V_{GS}=0\text{V}$)	V_{SD}	—	—	1.2	V
Zero Gate Voltage Drain Current 零柵壓漏極電流($V_{GS}=0\text{V}, V_{DS}= 16\text{V}$) ($V_{GS}=0\text{V}, V_{DS}= 16\text{V}, T_A=55^{\circ}\text{C}$)	I_{DSS}	—	—	1 10	μA
Gate Body Leakage 柵極漏電流($V_{GS}=\pm 8\text{V}, V_{DS}=0\text{V}$)	I_{GSS}	—	—	± 100	nA
Static Drain-Source On-State Resistance 靜態漏源導通電阻($I_D=3.3\text{A}, V_{GS}=4.5\text{V}$)	$R_{DS(ON)}$	—	50	60	$\text{m}\Omega$
Static Drain-Source On-State Resistance 靜態漏源導通電阻($I_D=2\text{A}, V_{GS}=2.5\text{V}$)	$R_{DS(ON)}$	—	70	80	$\text{m}\Omega$
Input Capacitance 輸入電容 ($V_{GS}=0\text{V}, V_{DS}= 6\text{V}, f=1\text{MHz}$)	C_{ISS}	—	—	550	pF
Common Source Output Capacitance 共源輸出電容($V_{GS}=0\text{V}, V_{DS}= 6\text{V}, f=1\text{MHz}$)	C_{OSS}	—	—	170	pF
Turn-ON Time 開啓時間 ($V_{DS}= 6\text{V}, I_D= 1\text{A}, R_{GEN}=6\Omega$)	$t_{(on)}$	—	—	20	ns
Turn-OFF Time 關斷時間 ($V_{DS}= 6\text{V}, I_D= 1\text{A}, R_{GEN}=6\Omega$)	$t_{(off)}$	—	—	65	ns